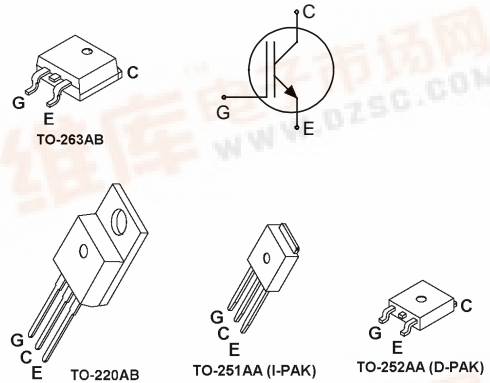




SGP02N60, SGB02N60 SGD02N60, SGU02N60

Fast S-IGBT in NPT-technology

- 75% lower E_{off} compared to previous generation combined with low conduction losses
- Short circuit withstand time – 10 μ s
- Designed for:
 - Motor controls
 - Inverter
- NPT-Technology for 600V applications offers:
 - very tight parameter distribution
 - high ruggedness, temperature stable behaviour
 - parallel switching capability



Type	V_{CE}	I_C	$V_{CE(sat)}$	T_j	Package	Ordering Code
SGP02N60	600V	2A	2.2V	150°C	TO-220AB	Q67041-A4707-A2
SGB02N60					TO-263AB	Q67041-A4707-A4
SGD02N60					TO-252AA(DPAK)	Q67041-A4707-A5
SGU02N60					TO-251AA(IPAK)	Q67041-A4707-A6

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current	I_C	6.0	A
$T_C = 25^\circ\text{C}$		6.0	
$T_C = 100^\circ\text{C}$		2.9	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	12	
Turn off safe operating area	-	12	
$V_{CE} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$			
Gate-emitter voltage	V_{GE}	± 20	V
Avalanche energy, single pulse	E_{AS}	13	mJ
$I_C = 2\text{ A}, V_{CC} = 50\text{ V}, R_{GE} = 25\ \Omega,$ start at $T_j = 25^\circ\text{C}$			
Short circuit withstand time ¹⁾	t_{SC}	10	μ s
$V_{GE} = 15\text{V}, V_{CC} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$			
Power dissipation	P_{tot}	30	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$



¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.



SGP02N60, SGB02N60 SGD02N60, SGU02N60

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		4.2	K/W
Thermal resistance, junction – ambient	R_{thJA}	TO-220AB	62	
SMD version, device on PCB ¹⁾	R_{thJA}	TO-263AB	40	

Electrical Characteristic, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=2A$	1.7	1.9	2.4	
		$T_j=150^\circ\text{C}$	-	2.2	2.7	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=150\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$	-	-	20	μA
		$T_j=150^\circ\text{C}$	-	-	250	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=2A$	-	1.6	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	$V_{CE}=25V, V_{GE}=0V, f=1\text{MHz}$	-	142	170	pF
Output capacitance	C_{oss}		-	18	22	
Reverse transfer capacitance	C_{riss}		-	10	12	
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=2A, V_{GE}=15V$	-	14	18	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	TO-220AB	-	7	-	nH
Short circuit collector current ²⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s, V_{CC}\leq 600V, T_j\leq 150^\circ\text{C}$	-	20	-	A

¹⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μ m thick) copper area for collector connection. PCB is vertical without blown air.

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.



SGP02N60, SGB02N60 SGD02N60, SGU02N60

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=2\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=118\Omega$,	-	20	24	ns
Rise time	t_r		-	13	16	
Turn-off delay time	$t_{d(off)}$		-	259	311	
Fall time	t_f		-	52	62	
Turn-on energy	E_{on}	Energy losses include "tail" and diode reverse recovery.	-	0.036	0.041	mJ
Turn-off energy	E_{off}		-	0.028	0.036	
Total switching energy	E_{ts}		-	0.064	0.078	

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=2\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=118\Omega$	-	20	24	ns
Rise time	t_r		-	14	17	
Turn-off delay time	$t_{d(off)}$		-	287	344	
Fall time	t_f		-	67	80	
Turn-on energy	E_{on}	Energy losses include "tail" and diode reverse recovery.	-	0.054	0.062	mJ
Turn-off energy	E_{off}		-	0.043	0.056	
Total switching energy	E_{ts}		-	0.097	0.118	

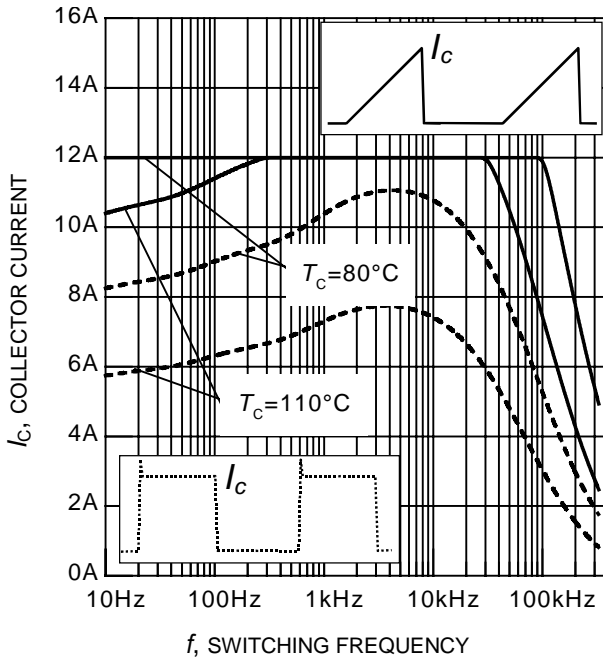


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/+15\text{V}$, $R_G = 118\Omega$)

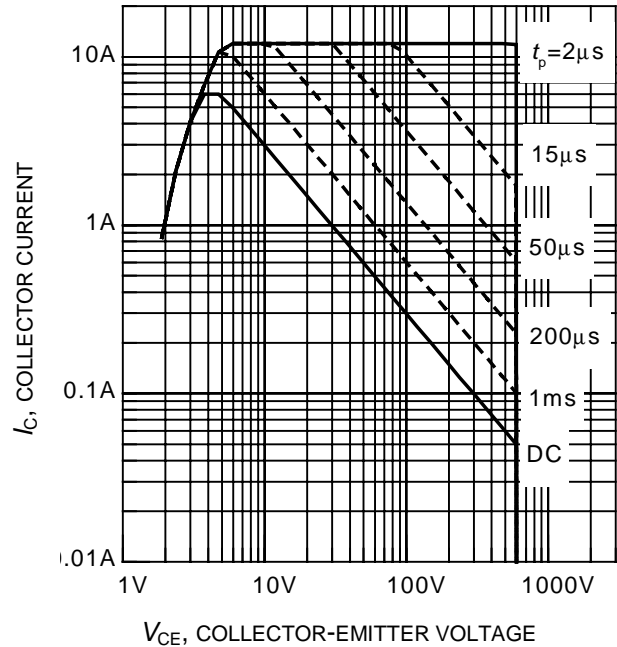


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

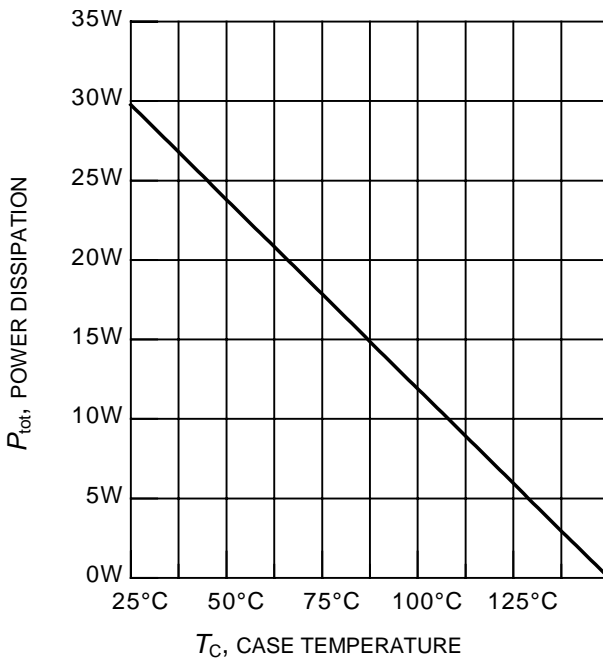


Figure 3. Power dissipation (IGBT) as a function of case temperature
 ($T_j \leq 150^\circ\text{C}$)

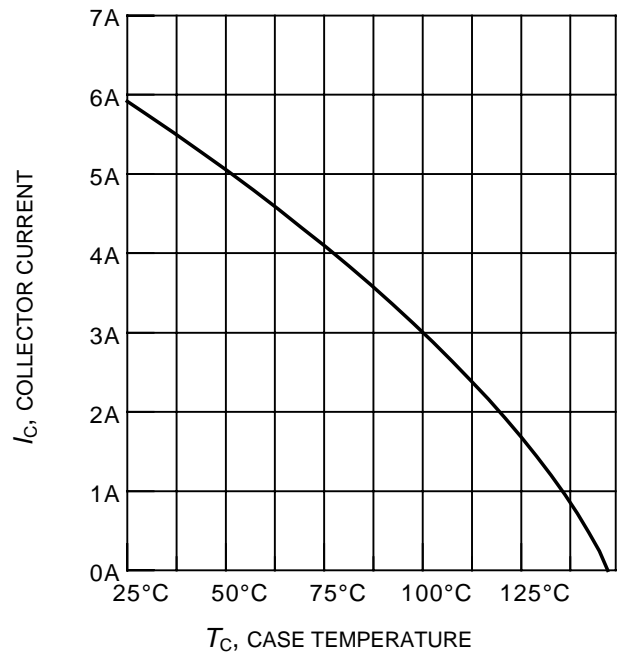


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

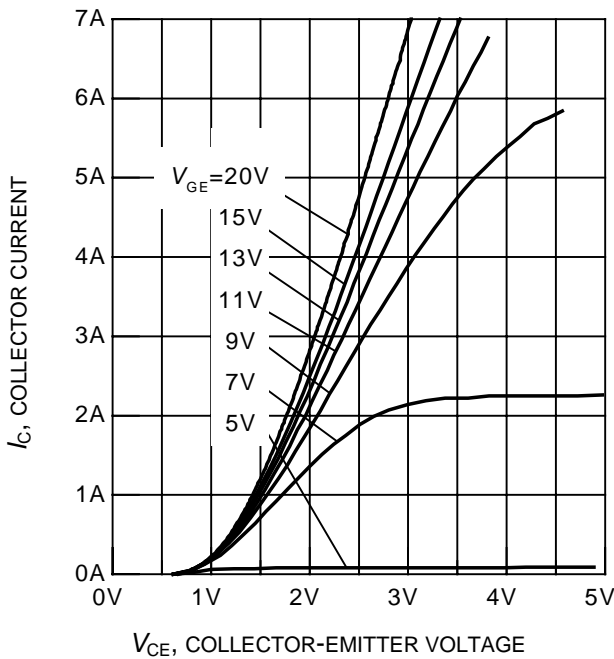


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

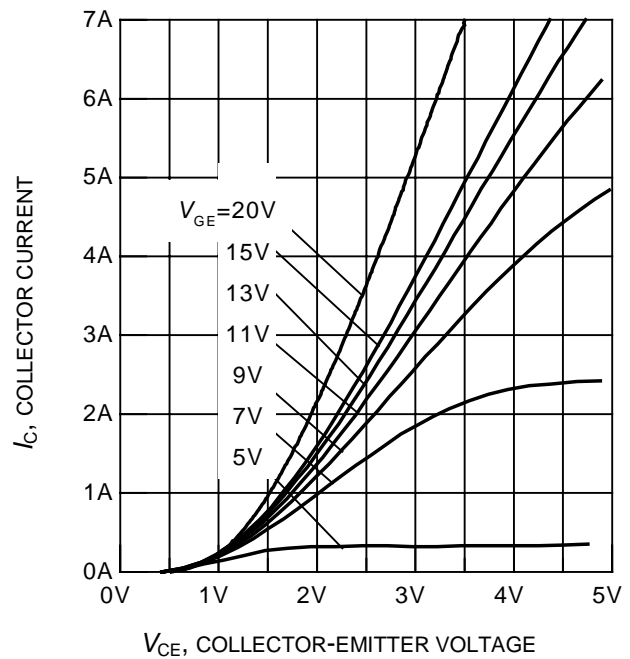


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

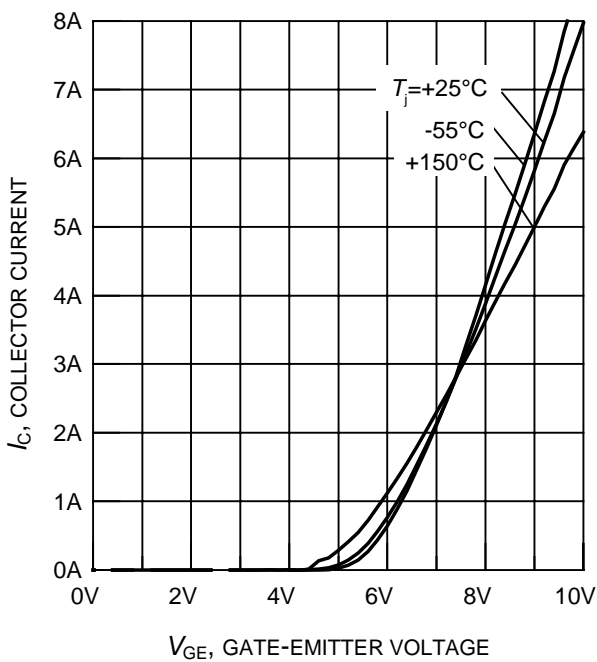


Figure 7. Typical transfer characteristics
($V_{CE} = 10\text{V}$)

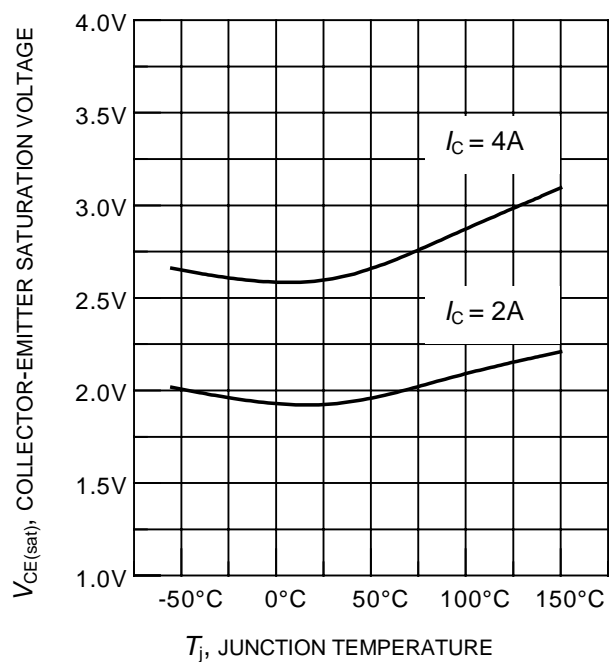


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

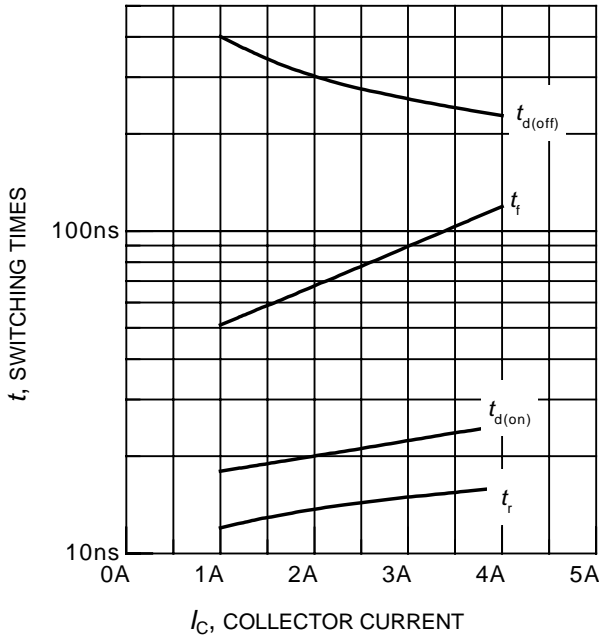


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 118\Omega$)

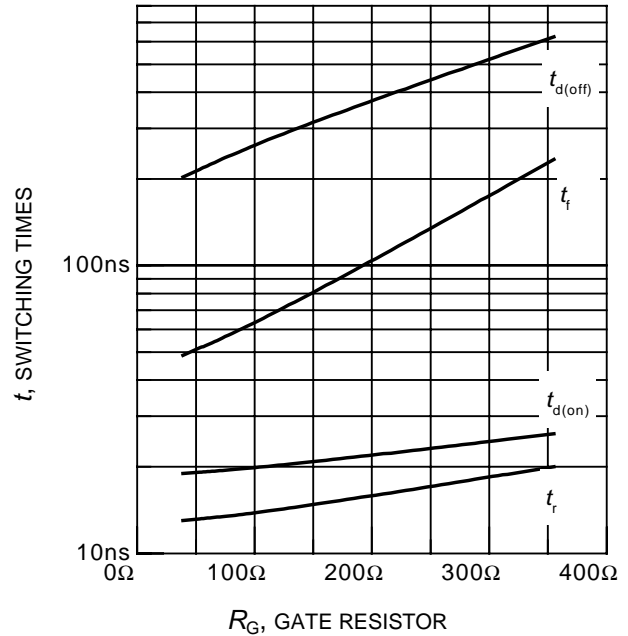


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 2\text{A}$)

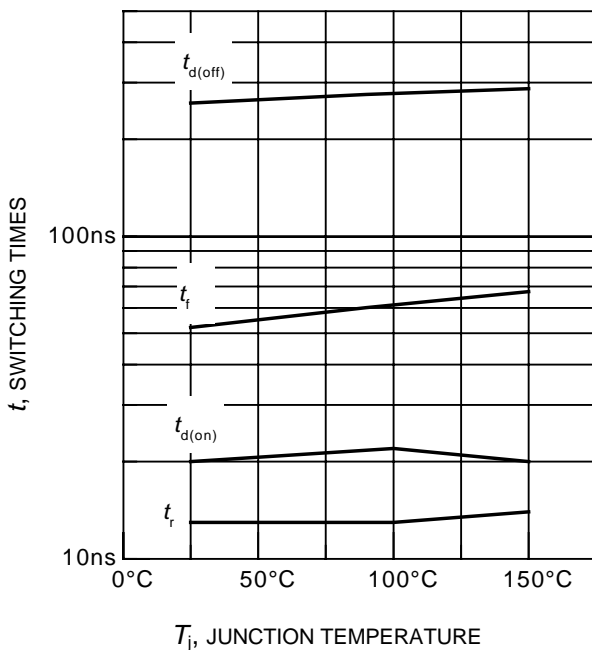


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 2\text{A}$, $R_G = 118\Omega$)

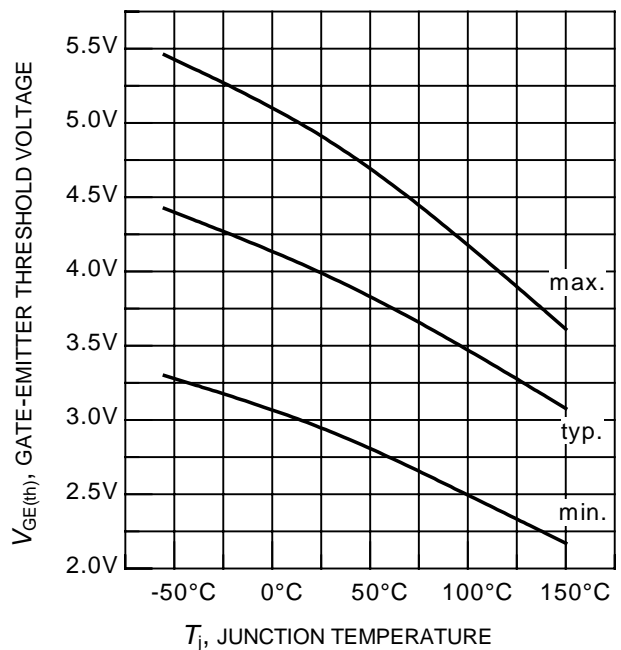


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 0.15\text{mA}$)

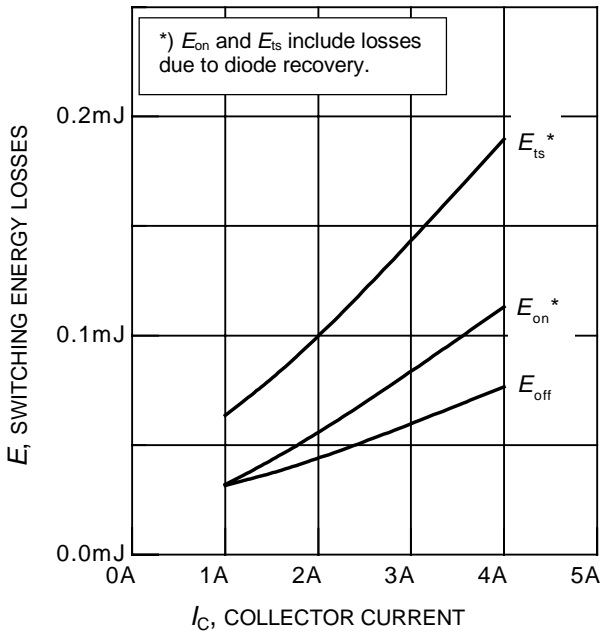


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 118\Omega$)

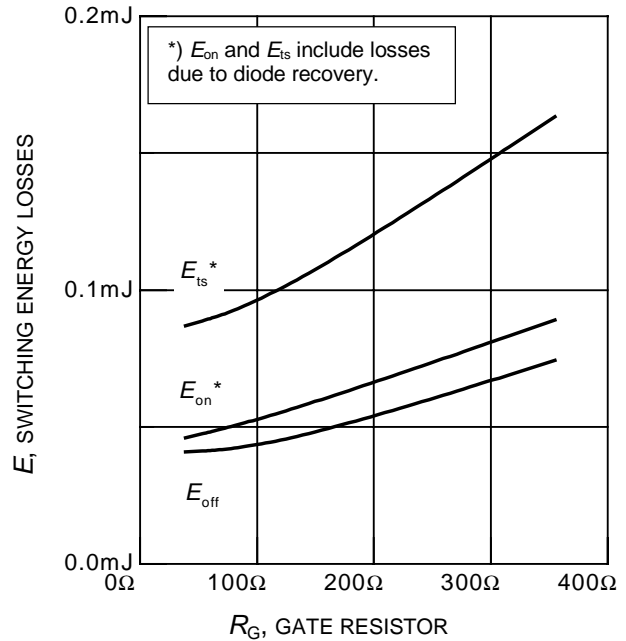


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 2\text{A}$)

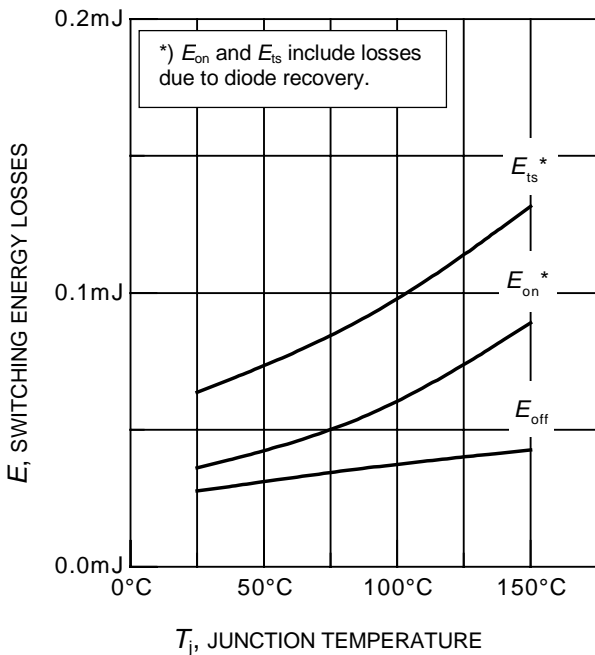


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 2\text{A}$, $R_G = 118\Omega$)

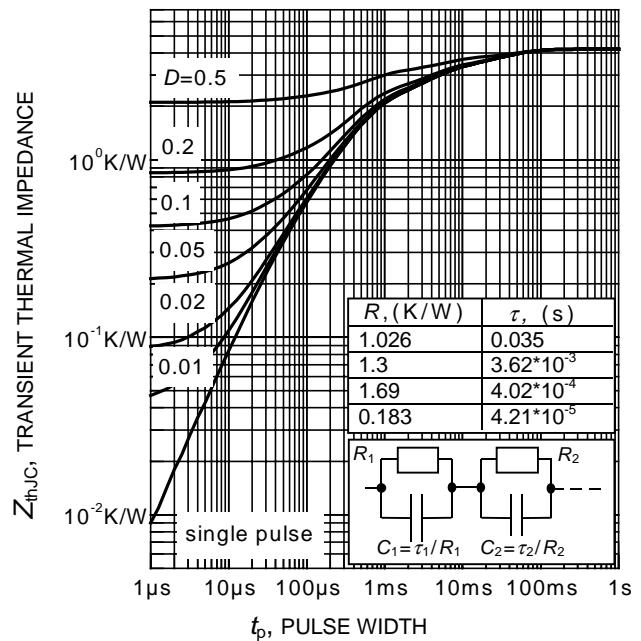


Figure 16. IGBT transient thermal impedance as a function of pulse width
($D = t_p / T$)

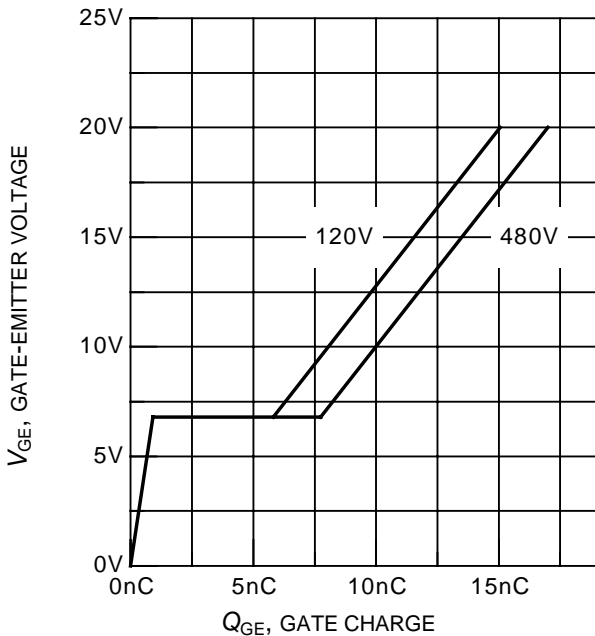


Figure 17. Typical gate charge
($I_C = 2A$)

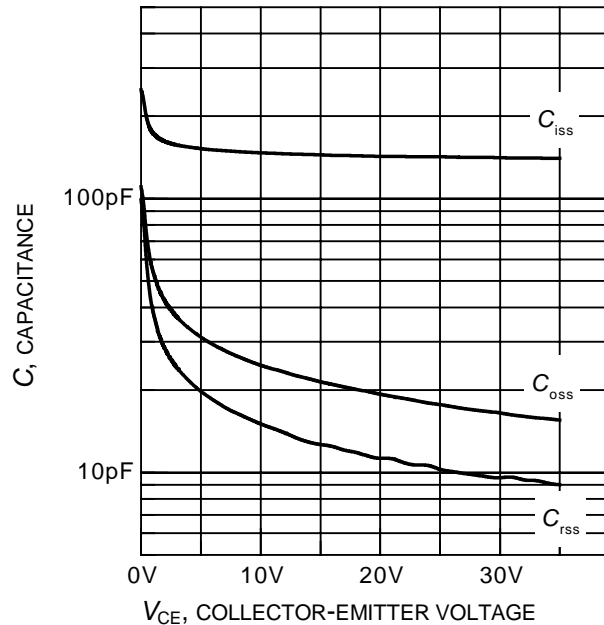


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE} = 0V, f = 1MHz$)

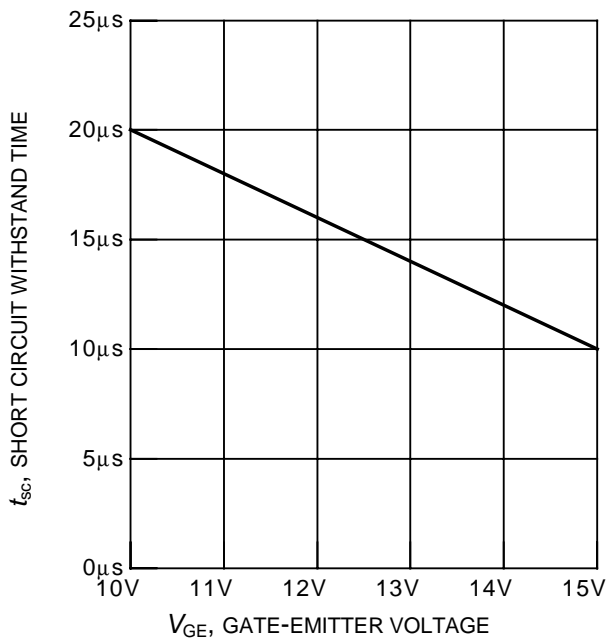


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE} = 600V, \text{start at } T_j = 25^\circ C$)

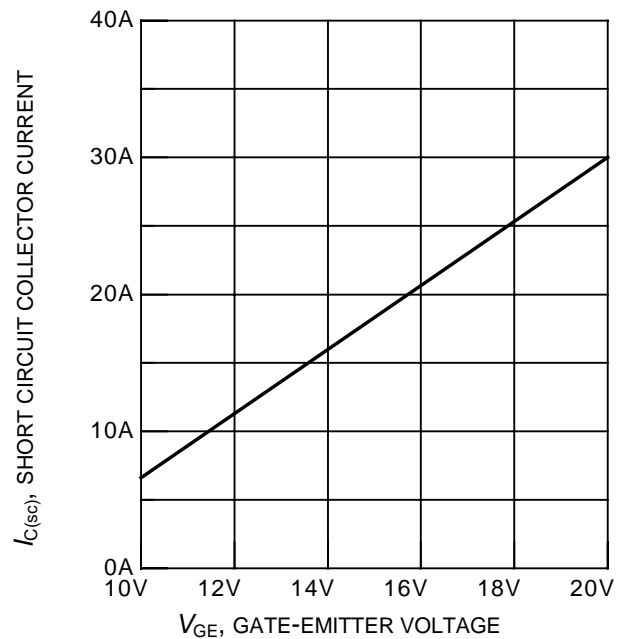
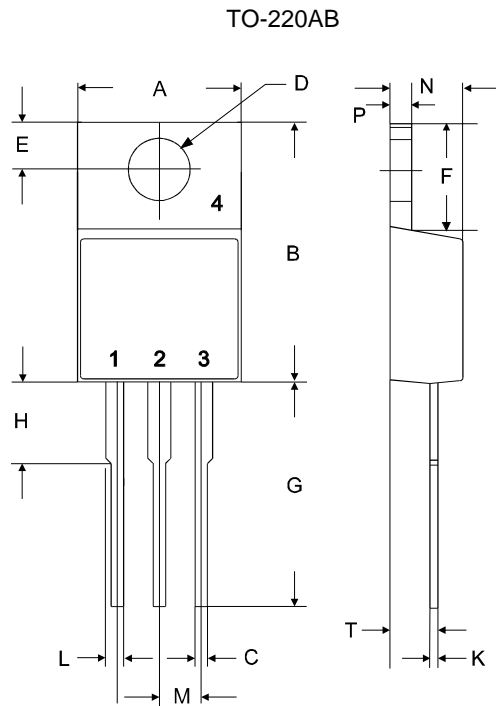
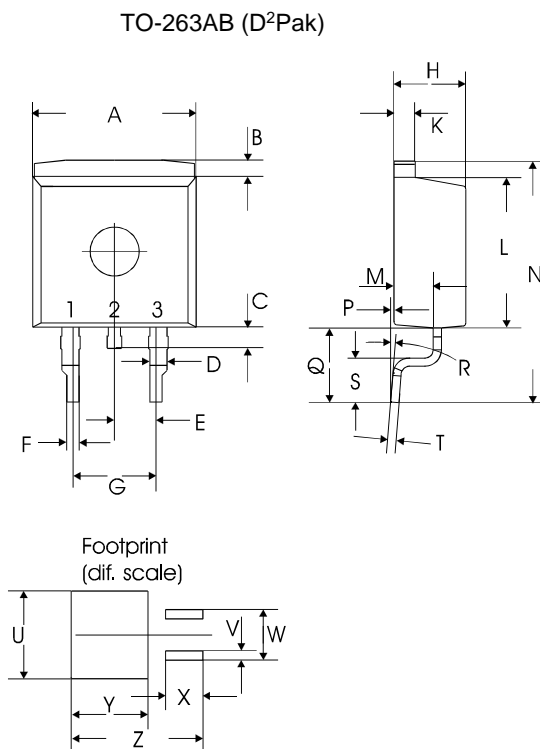


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600V, T_j = 150^\circ C$)

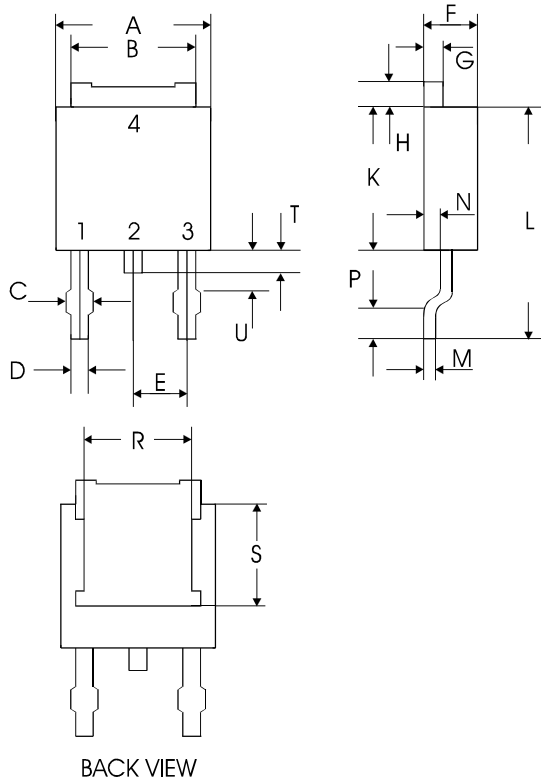


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071



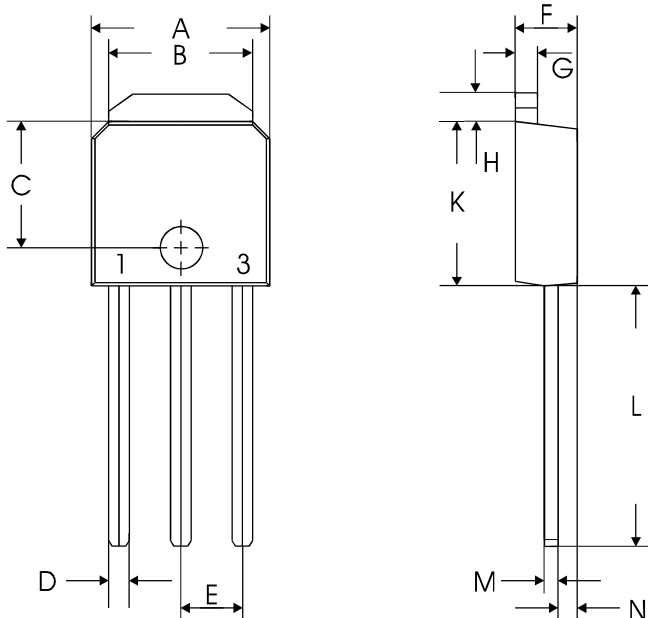
symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.20	0.3858	0.4016
B	0.70	1.30	0.0276	0.0512
C	1.00	1.60	0.0394	0.0630
D	1.03	1.07	0.0406	0.0421
E	2.54 typ.		0.1 typ.	
F	0.65	0.85	0.0256	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.17	1.37	0.0461	0.0539
L	9.05	9.45	0.3563	0.3720
M	2.30	2.50	0.0906	0.0984
N	15 typ.		0.5906 typ.	
P	0.00	0.20	0.0000	0.0079
Q	4.20	5.20	0.1654	0.2047
R	8° max		8° max	
S	2.40	3.00	0.0945	0.1181
T	0.40	0.60	0.0157	0.0236
U	10.80		0.4252	
V	1.15		0.0453	
W	6.23		0.2453	
X	4.60		0.1811	
Y	9.40		0.3701	
Z	16.15		0.6358	

P-TO252 (D-Pak)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	6.40	6.73	0.2520	0.2650
B	5.25	5.50	0.2067	0.2165
C	(0.65)	(1.15)	(0.0256)	(0.0453)
D	0.63	0.89	0.0248	0.0350
E	2.28		0.2520	
F	2.19	2.39	0.0862	0.0941
G	0.76	0.98	0.0299	0.0386
H	0.90	1.21	0.0354	0.0476
K	5.97	6.23	0.2350	0.2453
L	9.40	10.40	0.3701	0.4094
M	0.46	0.58	0.0181	0.0228
N	0.87	1.15	0.0343	0.0453
P	0.51	-	0.0201	-
R	5.00	-	0.1969	-
S	4.17	-	0.1642	-
T	0.26	1.02	0.0102	0.0402
U	-	-	-	-

P-TO251 (I-Pak)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	6.47	6.73	0.2547	0.2650
B	5.25	5.41	0.2067	0.2130
C	4.19	4.43	0.1650	0.1744
D	0.63	0.89	0.0248	0.0350
E	2.29 typ.		0.0902 typ.	
F	2.18	2.39	0.0858	0.0941
G	0.76	0.86	0.0299	0.0339
H	1.01	1.11	0.0398	0.0437
K	5.97	6.23	0.2350	0.2453
L	9.14	9.65	0.3598	0.3799
M	0.46	0.56	0.0181	0.0220
N	0.98	1.15	0.0386	0.0453

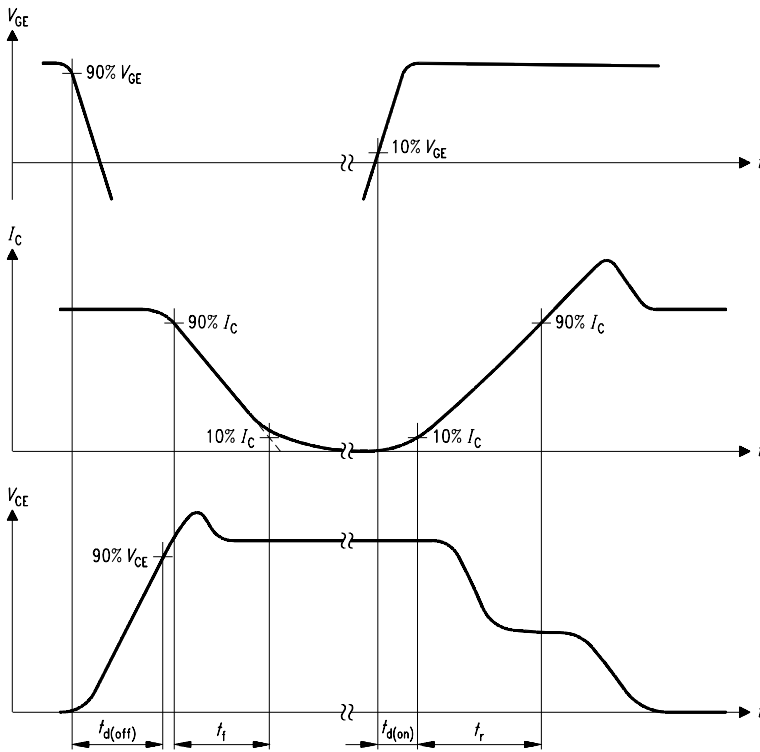


Figure A. Definition of switching times

SIS00053

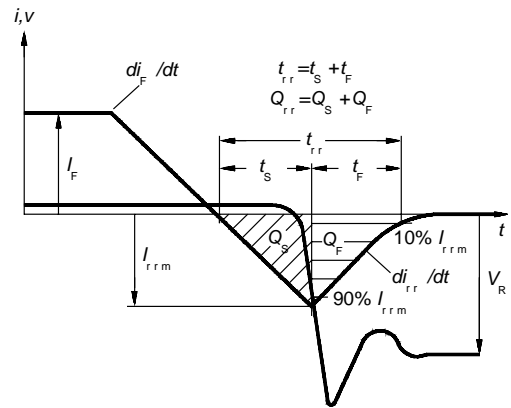


Figure C. Definition of diodes switching characteristics

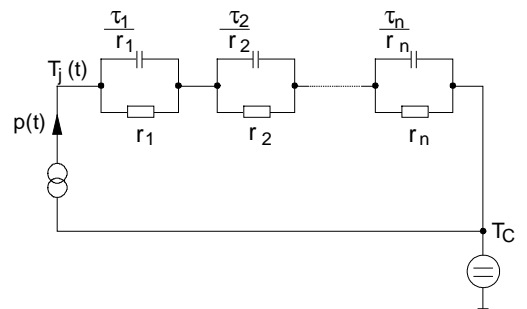


Figure D. Thermal equivalent circuit

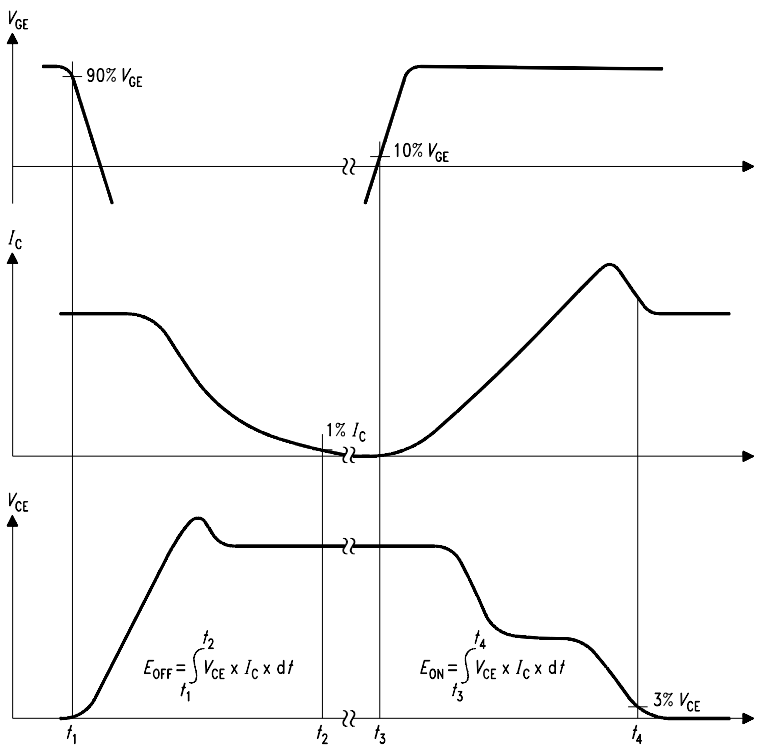


Figure B. Definition of switching losses

SIS00050



SGP02N60, SGB02N60 SGD02N60, SGU02N60

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